Xiaoliang Zhou

List of Publications by Year
in descending order

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31 papers	326 citations	840776 11 h-index	888059 17 g-index
31 all docs	31 docs citations	31 times ranked	292 citing authors

#	Article	IF	Citations
1	Oxygen Interstitial Creation in a-IGZO Thin-Film Transistors Under Positive Gate-Bias Stress. IEEE Electron Device Letters, 2017, 38, 1252-1255.	3.9	41
2	Room-Temperature-Processed Flexible Amorphous InGaZnO Thin Film Transistor. ACS Applied Materials & Interfaces, 2018, 10, 25850-25857.	8.0	36
3	Metal Reaction-Induced Bulk-Doping Effect in Forming Conductive Source-Drain Regions of Self-Aligned Top-Gate Amorphous InGaZnO Thin-Film Transistors. ACS Applied Materials & Interfaces, 2021, 13, 11442-11448.	8.0	33
4	Oxide Thin-Film Transistors With IMO and IGZO Stacked Active Layers for UV Detection. IEEE Journal of the Electron Devices Society, 2017, 5, 504-508.	2.1	22
5	Top-Gate Amorphous Indium-Gallium-Zinc-OxideThin-Film Transistors With Magnesium Metallized Source/Drain Regions. IEEE Transactions on Electron Devices, 2020, 67, 1619-1624.	3.0	19
6	Implementation of Self-Aligned Top-Gate Amorphous Zinc Tin Oxide Thin-Film Transistors. IEEE Electron Device Letters, 2019, 40, 901-904.	3.9	15
7	An Analytical Subthreshold Model of Polycrystalline Silicon Thin-Film Transistors Based on Meyer-Neldel Rule. IEEE Transactions on Electron Devices, 2014, 61, 863-869.	3.0	14
8	Oxygen Adsorption Effect of Amorphous InGaZnO Thin-Film Transistors. IEEE Electron Device Letters, 2017, 38, 465-468.	3.9	14
9	High-Performance Self-Aligned Top-Gate Amorphous InGaZnO TFTs With 4 nm-Thick Atomic-Layer-Deposited AlO_x Insulator. IEEE Electron Device Letters, 2022, 43, 729-732.	3.9	14
10	Nb Doped TiO₂Protected Back-Channel-Etched Amorphous InGaZnO Thin Film Transistors. IEEE Electron Device Letters, 2017, 38, 213-216.	3.9	13
11	Pâ€20: Effects of N₂O Plasma Treatment Time on the Performance of Selfâ€Aligned Topâ€Gate amorphous oxide Thin Film Transistors. Digest of Technical Papers SID International Symposium, 2017, 48, 1299-1302.	0.3	11
12	Abnormal Bias Instabilities Induced by Lateral H₂O Diffusion Into Top-Gate Insulator of a-InGaZnO Thin-Film Transistors. IEEE Journal of the Electron Devices Society, 2022, 10, 341-345.	2.1	11
13	Scalability and Stability Enhancement in Self-Aligned Top-Gate Indium- Zinc-Oxide TFTs With Al Reacted Source/Drain. IEEE Journal of the Electron Devices Society, 2018, 6, 680-684.	2.1	9
14	Homo-Junction Bottom-Gate Amorphous Inâ€“Gaâ€“Znâ€“O TFTs With Metal-Induced Source/Drain Regions. IEEE Journal of the Electron Devices Society, 2019, 7, 52-56.	2.1	9
15	Low temperature and high-performance ZnSnO thin-film transistors engineered by in situ thermal manipulation. Journal of Materials Chemistry C, 2022, 10, 3129-3138.	5.5	9
16	Nonlinear photocurrent-intensity behavior of amorphous InZnO thin film transistors. Applied Physics Letters, 2018, 112, .	3.3	8
17	Structure and stoichiometry evolution of sputtered Nb doped TiO2 films induced by O2 pressure variation during postannealing process. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2016, 34, .	2.1	7
18	Source-drain resistance characteristics of back-channel etched amorphous InGaZnO thin film transistors with TiO 2 :Nb protective layer. Materials Science in Semiconductor Processing, 2017, 68, 147-151.	4.0	7

#	Article	IF	Citations
19	Self-Heating Stress-Induced Severe Humps in Transfer Characteristics of Amorphous InGaZnO Thin-Film Transistors. IEEE Transactions on Electron Devices, 2021, 68, 6197-6201.	3.0	7
20	Self-Aligned Top-Gate Amorphous Zinc-Tin Oxide Thin-Film Transistor With Source/Drain Regions Doped by Al Reaction. IEEE Journal of the Electron Devices Society, 2021, 9, 653-657.	2.1	6
21	Roles of Hot Carriers in Dynamic Self-Heating Degradation of a-InGaZnO Thin-Film Transistors. IEEE Electron Device Letters, 2022, 43, 40-43.	3.9	6
22	Thorough Elimination of Persistent Photoconduction in Amorphous InZnO Thin-Film Transistor via Dual-Gate Pulses. IEEE Electron Device Letters, 2022, 43, 1247-1250.	3.9	4
23	Pâ€45: Effect of Ar / O₂ Flow Ratio during Sputtering of InZnO Active Layer on Photocurrent and Responsivity Characteristics of Amorphous InZnO Thin Film Transistors. Digest of Technical Papers SID International Symposium, 2020, 51, 1515-1518.	0.3	3
24	Self-Compensation Effect of Photo-Bias Instabilities in a-InGaZnO Thin-Film Transistors Induced by Unique Ion Migration. IEEE Transactions on Electron Devices, 2022, 69, 3206-3212.	3.0	3
25	Competition between heating and cooling during dynamic self-heating degradation of amorphous InGaZnO thin-film transistors. Solid-State Electronics, 2022, 195, 108393.	1.4	3
26	A Physical-Based Analytical Model for the Kink Current of Polycrystalline Silicon TFTs. IEEE Transactions on Electron Devices, 2020, 67, 2359-2364.	3.0	1
27	Pâ€1.15: Short time negative gate voltage pulse to eliminate persistent photoconductivity in Amorphous InZnO thin film transistors. Digest of Technical Papers SID International Symposium, 2021, 52, 452-452.	0.3	1
28	TiO<inf>2</inf>:Nb film thickness influences on the amorphous InGaZnO thin film transistors with Mo/TiO2:Nb source-drain electrodes. , 2017, , .		0
29	Ti Film Thickness Influences on the Back Channel Etched Amorphous InGaZnO<inf>4</inf> Thin Film Transistors. , 2018, , .		0
30	Pâ€1.12: Effects of Gate Voltage Pulse Width and Amplitude on Eliminating Persistent Photoconductivity in Amorphous InZnO TFTs. Digest of Technical Papers SID International Symposium, 2021, 52, 703-706.	0.3	0
31	Fully Self-Aligned Homojunction Bottom-Gate Amorphous InGaZnO TFTs with Al Reacted Source/Drain Regions. , 2020, , .		0